Haizheng Song

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Interface Trap-Induced Nonideality in As-Deposited Ni/4H-SiC Schottky Barrier Diode. IEEE Transactions on Electron Devices, 2015, 62, 615-621.	3.0	33

2 Synthesis and characterization of volatile metal Î²-diketonate chelates of M(DPM)n (M=Ce, Gd, Y, Zr,) Tj ETQq0 0 0 rgBT /Overlock 10 Tf

3	Decomposition Behavior of M(DPM)n (DPM = 2,2,6,6-Tetramethyl-3,5-heptanedionato; n = 2, 3, 4). Journal of Physical Chemistry A, 2006, 110, 13479-13486.	2.5	26
4	Basal plane dislocation conversion near the epilayer/substrate interface in epitaxial growth of 4° off-axis 4H–SiC. Journal of Crystal Growth, 2013, 371, 94-101.	1.5	25
5	Nonlinear Kinetics of GaAs MOVPE Examined by Selective Area Growth Technique. Journal of the Electrochemical Society, 2007, 154, H91.	2.9	21
6	Large barrier, highly uniform and reproducible Ni-Si/4H-SiC forward Schottky diode characteristics: testing the limits of Tung's model. Journal Physics D: Applied Physics, 2014, 47, 295102.	2.8	21
7	Investigations of defect evolution and basal plane dislocation elimination in CVD epitaxial growth of silicon carbide on eutectic etched epilayers. Journal of Crystal Growth, 2011, 320, 95-102.	1.5	16
8	Effect of Surface Misorientation on the Kinetics of GaAs MOVPE Examined Using Selective Area Growth. Electrochemical and Solid-State Letters, 2006, 9, G104.	2.2	15
9	Deposition of Y2O3 stabilized ZrO2 thin films from Zr(DPM)4 and Y(DPM)3 by aerosol-assisted MOCVD. Materials Letters, 2003, 57, 3833-3838.	2.6	14
10	Synthesis and characterization of Sm(DPM)3 used as precursor for MOCVD. Journal of Crystal Growth, 2004, 267, 256-262.	1.5	13
11	Effect of group V partial pressure on the kinetics of selective area MOVPE for GaAs on (100) exact and misoriented substrate. Journal of Crystal Growth, 2006, 287, 664-667.	1.5	13
12	Deposition of Sm2O3 doped CeO2 thin films from Ce(DPM)4 and Sm(DPM)3 (DPM=2,2,6,6-tetramethyl-3,5-heptanedionato) by aerosol-assisted metal–organic chemical vapor deposition. Thin Solid Films, 2006, 510, 88-94.	1.8	13
13	Formation and Rate Processes of Y[sub 2]O[sub 3] Stabilized ZrO[sub 2] Thin Films from Zr(DPM)[sub 4] and Y(DPM)[sub 3] by Cold-Wall Aerosol-Assisted MOCVD. Journal of the Electrochemical Society, 2005, 152, C498.	2.9	12
14	4H–SiC homoepitaxy on nearly on-axis substrates using TFS-towards high quality epitaxial growth. Journal of Crystal Growth, 2016, 448, 97-104.	1.5	12
15	Glide of threading edge dislocations after basal plane dislocation conversion during 4H–SiC epitaxial growth. Journal of Crystal Growth, 2015, 418, 7-14.	1.5	11
16	Non-linear kinetic analysis on GaAs selective area MOVPE combined with macro-scale analysis to extract major reaction mechanism. Journal of Crystal Growth, 2007, 298, 32-36.	1.5	9
17	Basal Plane Dislocation Mitigation in SiC Epitaxial Growth by Nondestructive Substrate Treatment. Crystal Growth and Design, 2012, 12, 1703-1707.	3.0	7
18	Study of Surface Morphology, Impurity Incorporation and Defect Generation during Homoepitaxial Growth of 4H-SiC Using Dichlorosilane. ECS Journal of Solid State Science and Technology, 2015, 4, P71-P76.	1.8	6

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#	Article	IF	CITATIONS
19	Trade-Off between Parasitic Deposition and SiC Homoepitaxial Growth Rate Using Halogenated Si-Precursors. ECS Journal of Solid State Science and Technology, 2013, 2, N3079-N3086.	1.8	5
20	Surface Reaction Kinetics of InP and InAs Metalorganic Vapor Phase Epitaxy Analyzed by Selective Area Growth Technique. Japanese Journal of Applied Physics, 2008, 47, 7788.	1.5	3
21	Nonlinear Kinetic Analysis of InP and InAs Metal Organic Vapor Phase Epitaxy by Selective Area Growth Technique. Japanese Journal of Applied Physics, 2008, 47, 8269-8274.	1.5	3
22	Reactor-scale uniformity of selective-area performance in InGaAsP system. Journal of Crystal Growth, 2007, 298, 59-63.	1.5	2
23	Non-linear surface reaction kinetics in GaAs selective area MOVPE. Journal of Crystal Growth, 2008, 310, 4731-4735.	1.5	2
24	Impact of Atomistic Surface Structure on Macroscopic Surface Reaction Rate in MOVPE of GaAs. Electrochemical and Solid-State Letters, 2007, 10, H123.	2.2	1
25	Effects of Zn- and S-Doping on Kinetics of GaAs Selective Area MOVPE. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	1
26	Kinetic Analysis of InAsP by Metalorganic Vapor Phase Epitaxy Selective Area Growth Technique. Japanese Journal of Applied Physics, 2009, 48, 041102.	1.5	1
27	Site Specific TEM Specimen Preparation for Characterization of Extended Defects in 4H-SiC Epilayers. Microscopy and Microanalysis, 2014, 20, 344-345.	0.4	0